

ABSTRACT OF THE DISCLOSURE

Sensing devices for sensing a programmed state of a floating-gate memory cell are adapted for use in low-power memory devices using supply potentials that can be significantly higher than the maximum potential to be achieved on a local bit line during a sensing operation. Such sensing devices include an input node selectively coupled to a floating-gate memory cell and an output node for providing an output signal indicative of the programmed state of the floating-gate memory cell. Such sensing devices further include a feedback loop coupled between a precharge path and the input node of the sensing device. The feedback loop limits the potential level achieved at the input node of the sensing device, thus limiting the potential level achieved by the bit lines during sensing.